

シリコンカーバイドウエハー (SiC Wafer)
4 インチ 高純度半絶縁型 4H-SiC ウエハー

SICC



Diameter	100.0 mm+0.0/-0.5 mm
Surface Orientation	{0001} ± 0.2°
Primary Flat Orientation	<11-20> ± 5.0°
Secondary Flat Orientation	90.0° CW from Primary ± 5.0° Silicon face up
Primary Flat Length	32.5 mm ± 2.0 mm
Secondary Flat Length	18.0 mm ± 2.0 mm
Wafer Edge	Chamfer
Micropipe Density	≤5 micropipes/ cm ²
Resistivity	≥1E5 Ω·cm
Thickness	350.0 μm ± 25.0 μm 500.0 μm ± 25.0 μm
TTV	≤10 μm
Bow (absolute value)	≤25 μm
Warp	≤45 μm
Surface Roughness	CMP Si Face Ra≤0.5 nm
Cracks by high intensity light	None permitted
Edge chips /indents by diffuse lighting	None permitted
Total usable area	≥90%
Impurity concentration	≤ 5E16 cm ⁻³ Including V ≤ 1E14 cm ⁻³